



B-24314-C2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

JOSEPH T. EVANS, JR. ET AL.

Serial No.:

582,672

Filed:

September 14, 1990

Group:

233

For:

NON-VOLATILE MEMORY CIRCUIT USING  
FERROELECTRIC CAPACITOR STORAGE ELEMENT

Honorable Commissioner of  
Patents and Trademarks  
Washington, D.C. 20231

Dear Sir:

SECOND PRELIMINARY AMENDMENT AND REQUEST  
FOR DECLARATION OF INTERFERENCE UNDER RULE 1.607

Please amend the above-referenced application as follows:

IN THE CLAIMS

Please add the following claims:

472. In a nonvolatile ferroelectric memory of the type having a plurality of memory cells, a bit line coupled to each said memory cell, each said memory cell comprising a ferroelectric capacitor having first and second plate electrodes, the polarization of said capacitors corresponding to the data stored therewithin, the improvement wherein:

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:  
Commissioner of Patents and Trademarks,

Washington, D.C. 20231 on October 10, 1990  
(Date of Deposit)

Roger N. Chauza, Reg. No. 29,753

Name of applicant, assignee, or  
Registered Representative

Signature

Date of Signature